

2012 International Symposium on Dry Process

Program

Thursday, November 15, 2012

Opening Remarks (9:30–9:40) H. Kokura (Fujitsu Semiconductor Ltd.)

Best/Young Award Ceremony (9:40–9:50) Presenter: M. Izawa (Hitachi High-technologies Corp.)

Nishizawa Award Lectures 9:50–10:50
 Chairperson: T. Ichiki (Univ. of Tokyo)
 H. H. Sawin (Massachusetts Institute of Technology) 9:50–10:20
 R. A. Gottscho (Lam Research Corp.) 10:20–10:50

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Session A Surface Reaction (11:10–12:30)

Chairpersons: K. Nojiri (Lam Research Corp.), K. Karahashi (Osaka Univ.)

- [A-1] Roughness formation mechanisms involved in HBr cure 11:10–11:30
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Chairpersons: M. Shiratani (Kyushu Univ.), M. Nakatani (Panasonic Corp.)

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 T. Shimizu¹, G. Isbary², J. L. Zimmermann¹, S. Karrer³, W. Stolz², G. E. Morfill¹
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Chairpersons: T. Nozaki (Tokyo Inst. of Tech), E. Stamate (Tech. Univ. of Denmark)

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Chairpersons: H. Toyoda (Nagoya Univ.), N. Negishi (Hitachi Ltd.)

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N. Negishi (Hitachi, Ltd.)